**Product data sheet** 

# 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a SOT323 (SC-70) small Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Low R<sub>DSon</sub>
- Very fast switching
- Trench MOSFET technology

# 3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
$V_{GS}$	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> 25 °C	[1]	-	-	-1	Α
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -1 A; $T_j$ = 25 °C		-	175	200	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	1 2	G S
			SC-70 (SOT323)	017aaa094

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMF170XP	SC-70	plastic surface-mounted package; 3 leads	SOT323			

# 7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMF170XP	XD%

<sup>[1] % =</sup> placeholder for manufacturing site code

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> 25 °C	[1]	-	-1	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-0.7	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-4	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	290	mW
			[1]	-	360	mW
		$T_{sp} = 25  ^{\circ}C$		-	1670	mW
Tj	junction temperature			-55	150	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain diode						
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-0.4	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

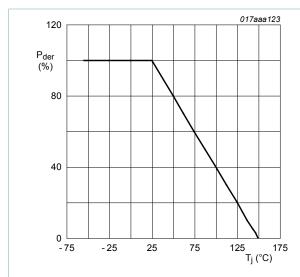


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

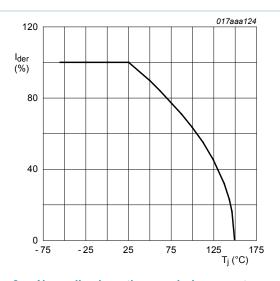
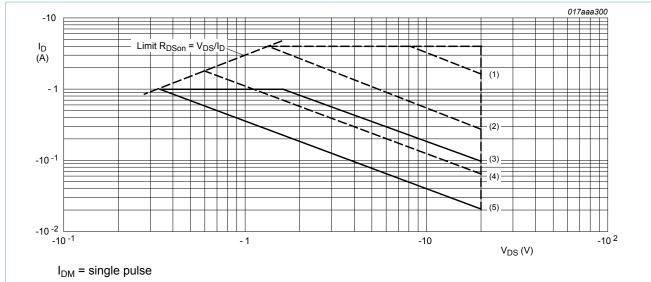


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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(1)  $t_p = 1 \text{ ms}$ 

(2)  $t_p = 10 \text{ ms}$ 

(3) DC;  $T_{sp} = 25 \,^{\circ}\text{C}$ 

(4)  $t_p = 100 \text{ ms}$ 

(5) DC;  $T_{amb} = 25 \, ^{\circ}\text{C}$ ; drain mounting pad 6 cm<sup>2</sup>

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	377	430	K/W
			[2]	-	305	350	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	65	75	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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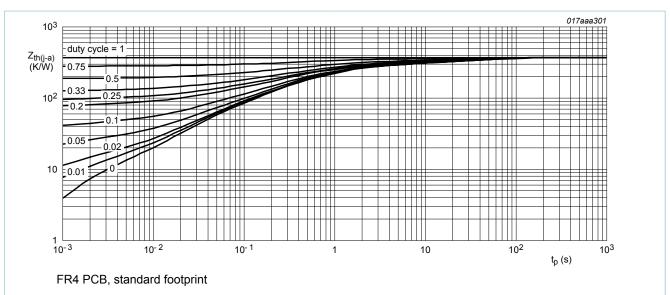


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

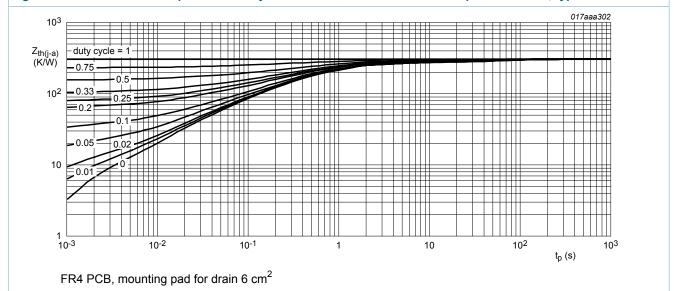


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static characteristics								
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		-20	-	-	V	
$V_{GSth}$	gate-source threshold voltage	I <sub>D</sub> = -250 A; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C		-0.65	-0.9	-1.15	V	
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C		-	-	-1	μA	
		V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C		-	-	-10	μA	
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -12 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-100	nA
		V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -1 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	175	200	mΩ
	resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -1 A; T <sub>j</sub> = 150 °C	-	250	284	mΩ
		$V_{GS}$ = -2.5 V; $I_D$ = -1 A; $T_j$ = 25 °C	-	240	300	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS} = -5 \text{ V}; I_{D} = -1 \text{ A}; T_{j} = 25 \text{ °C}$	-	1.9	-	S
Dynamic cl	haracteristics		'			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; $I_{D}$ = -1 A; $V_{GS}$ = -4.5 V; $T_{j}$ = 25 °C	-	2.6	3.9	nC
Q <sub>GS</sub>	gate-source charge		-	0.63	-	nC
$Q_{GD}$	gate-drain charge		-	0.53	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	280	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	43	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	30	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $I_{D}$ = -1 A; $V_{GS}$ = -4.5 V;	-	10	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	16	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	31	-	ns
t <sub>f</sub>	fall time		-	13	-	ns
Source-dra	in diode				-	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -0.4 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	-0.7	-1.2	V

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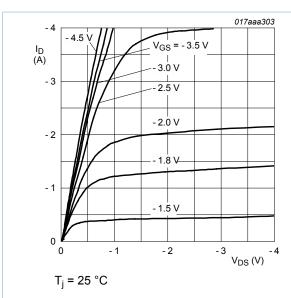
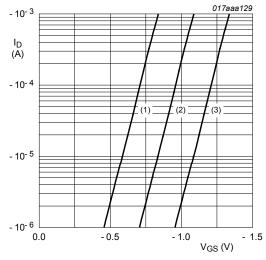


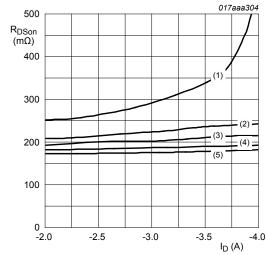
Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



$$T_i = 25 \,^{\circ}\text{C}; \, V_{DS} = -3 \,^{\circ}\text{V}$$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



$$(1) V_{GS} = -2.5 V$$

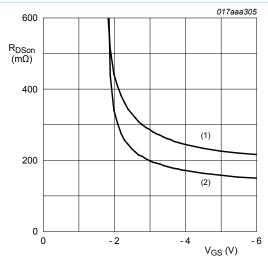
$$(2) V_{GS} = -3.0 V$$

$$(3) V_{GS} = -3.5 V$$

$$(4) V_{GS} = -4.0 V$$

$$(5) V_{GS} = -4.5 V$$

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

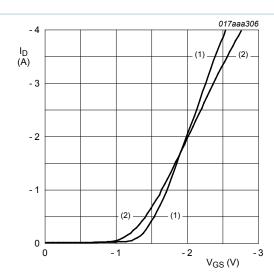


(1) 
$$T_i = 150 \, ^{\circ}C$$

(2) 
$$T_i = 25 \, ^{\circ}C$$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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 $V_{DS} > I_{D} \times R_{DSon}$ 

(1)  $T_j = 25 \,^{\circ}\text{C}$ (2)  $T_i = 150 \,^{\circ}\text{C}$ 

Fig. 10. Transfer characteristics: drain current as a

function of gate-source voltage; typical values

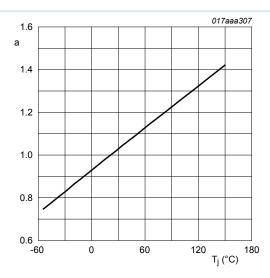
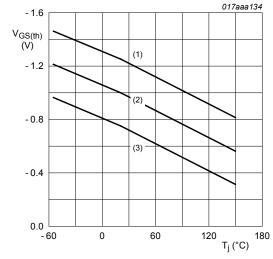


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

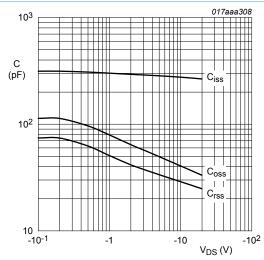
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values





 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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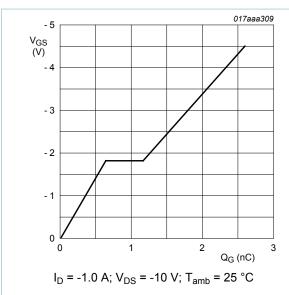


Fig. 14. Gate-source voltage as a function of gate charge; typical values

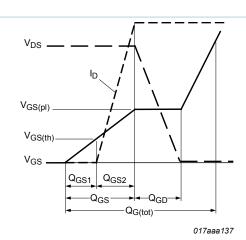
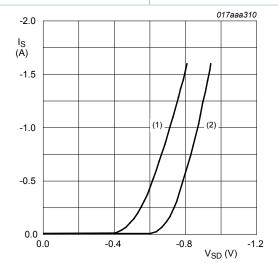


Fig. 15. Gate charge waveform definitions



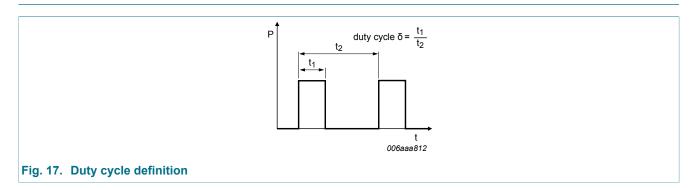
 $V_{GS} = 0 V$ (1)  $T_j = 150 \,^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

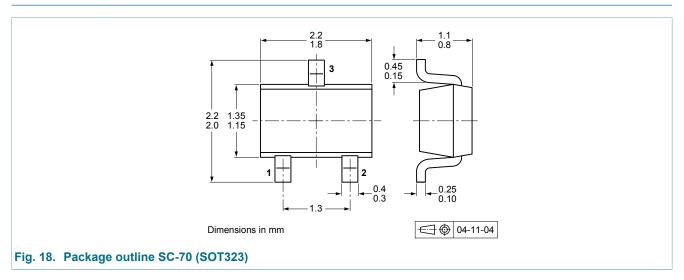
Fig. 16. Source current as a function of source-drain voltage; typical values

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# 11. Test information

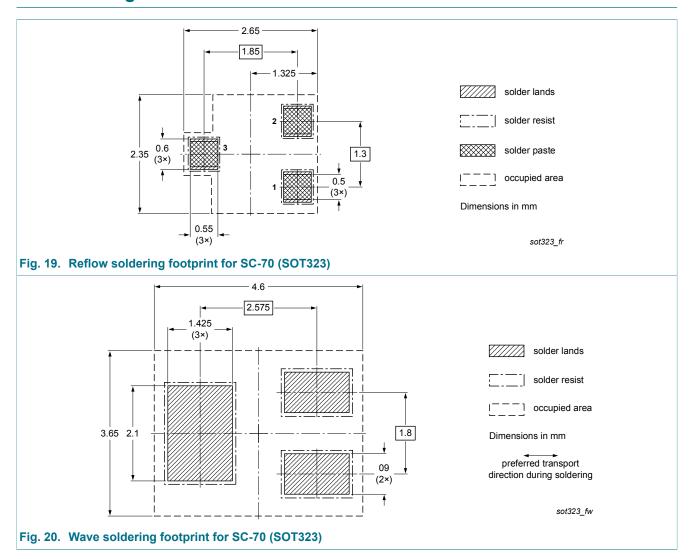


# 12. Package outline



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# 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMF170XP v.2	20131029	Product data sheet	-	PMF170XP v.1
Modifications:	Figure 13 corrected			
PMF170XP v.1	20110902	Product data sheet	-	-

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## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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